

Component [⊖]	Range [⊖]	Parameter Description [⊖]
BJT [⊖]	- [⊖]	hFE(DC Current Gain), Ube(Base-Emitter Voltage), Ic(Collector Current), Iceo(Collector Cut-off Current (IB=0)), Ices(Collector short Current), Uf(Forward Voltage of protecting diode) ③ [⊖]
Diode [⊖]	Forward Voltage <4.50V [⊖]	Forward Voltage, Diode Capacitance, Ir(Reverse Current) ② [⊖]
Double Diodes [⊖]		Forward Voltage [⊖]
Zener Diode [⊖]	0.01-4.50V [⊖] (Transistor test area) [⊖]	Forward Voltage, Reverse Voltage [⊖]
	0.01-30V [⊖] (Zener Diode test area) [⊖]	Reverse Voltage [⊖]
MOSFET [⊖]	JFET [⊖]	Cg(Gate Capacitance), Id(Drain Current) at Vgs(Gate to Source Threshold Voltag), Uf(Forward Voltage of protecting diode) ④ [⊖]
	IGBT [⊖]	Id(Drain Current) at Vgs(Gate to Source Threshold Voltag), Uf(Forward Voltage of protecting diode) ④ [⊖]
	MOSFET [⊖]	Vt(Gate to Source Threshold Voltag), Cg(Gate Capacitance), Rds(Drain to Source On Resistance), Uf(Forward Voltage of protecting diode) ④ [⊖]
Thyristor [⊖]	Igt(Gate trigger current)<6mA [⊖]	Gate trigger voltage [⊖]
Triac [⊖]		
Capacitor [⊖]	25pF-100mF [⊖]	Capacitance, ESR(Equivalent Series Resistance), Vloss ① [⊖]
Resistor [⊖]	0.01-50M Ω [⊖]	Resistance [⊖]
Inductor [⊖]	0.01mH-20H [⊖]	Inductance, DC Resistance ⑤ [⊖]
Battery [⊖]	0.1-4.5V [⊖]	Voltage, Battery Polarity [⊖]